

# **CGD944C**

# 870 MHz, 25 dB gain power doubler amplifier Rev. 01 — 6 June 2007

**Product data sheet** 

## **Product profile**

## 1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V (DC), employing Hetero Field Effect Transistor (HFET) GaAs dies.

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

#### 1.2 Features

- High output capability
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Rugged construction
- Gold metallization ensures excellent reliability

## 1.3 Applications

■ CATV systems operating in the 40 MHz to 870 MHz frequency range

## 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$G_p$	power gain	f = 870 MHz	24	25	26	dB
I <sub>tot</sub>	total current	$V_{B} = 24 \text{ V}$	[1]	450	-	mA

[1] Direct Current (DC)



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## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	input		
2, 3	common	1 3 5 7 9	5
5	+V <sub>B</sub>		$\frac{1}{2}$
7, 8	common		12 3 7 8
9	output		sym095

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
CGD944C	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J		

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 , ,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
$V_B$	supply voltage		-	30	V
V <sub>i(RF)</sub>	RF input voltage	single tone	-	75	dBmV
		132 channels flat	-	45	dBmV
T <sub>stg</sub>	storage temperature		-40	+100	°C
T <sub>mb</sub>	mounting base temperatur	е	-20	+100	°C

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## 5. Characteristics

Table 5. Characteristics

Bandwidth to 870 MHz;  $V_B = 24 \text{ V (DC)}$ ;  $T_{mb} = 35 \,^{\circ}\text{C}$ ; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 870 MHz		24	25	26	dB
SL <sub>sl</sub>	slope straight line	f = 40 MHz to 870 MHz	<u>[1]</u>	1	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 870 MHz	[2]	-	0.5	-	dB
СТВ	composite triple beat	79 + 53 flat NTSC channels	[3]	-	-68	-66	dB
		98 flat PAL channels	<u>[4]</u>	-	-66	-	dB
CSO	composite second-order distortion	79 + 53 flat NTSC channels	<u>[3]</u>	-	-70	-67	dB
		98 flat PAL channels	<u>[4]</u>	-	-66	-	dB
Xmod	cross modulation	79 + 53 flat NTSC channels	[3]	-	-66	-58	dB
RL <sub>in</sub> input ref	input return loss	f = 40 MHz to 80 MHz		20	-	-	dB
		f = 80 MHz to 160 MHz		19	-	-	dB
		f = 160 MHz to 320 MHz		18	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
RLout	output return loss	f = 40 MHz to 80 MHz		20	-	-	dB
		f = 80 MHz to 160 MHz		19	-	-	dB
		f = 160 MHz to 320 MHz		18	-	-	dB
		f = 320 MHz to 640 MHz		18	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
NF	noise figure	f = 50 MHz		-	3.5	5.0	dB
		f = 870 MHz		-	3.5	5.0	dB
I <sub>tot</sub>	total current	V <sub>B</sub> = 24 V	<u>[5]</u>	-	450	-	mA

<sup>[1]</sup>  $G_p$  at 870 MHz minus  $G_p$  at 40 MHz.

<sup>[2]</sup> flatness straight line (peak to valley).

<sup>[3] 79</sup> NTSC channels: 55.25 MHz to 547.25 MHz, 48 dBmV output level; + 53 NTSC channels 553.25 MHz to 997.25 MHz, 38 dBmV output level.

<sup>[4]</sup>  $V_0 = 48 \text{ dBmV}$ 

<sup>[5]</sup> Direct Current (DC)

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## 6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

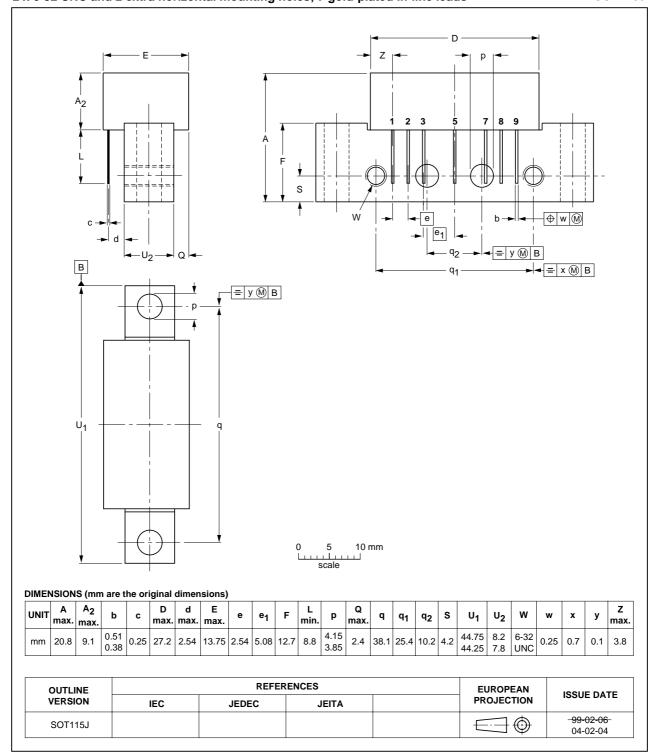


Fig 1. Package outline SOT115J

## 870 MHz, 25 dB gain power doubler amplifier

## 7. Abbreviations

Table 6. Abbreviations

Acronym	Description
CATV	CAble TeleVision
DC	Direct Current
NTSC	National Television Standard Committee
PAL	Phase-Alternation Line
RF	Radio Frequency
UNC	UNified Coarse thread

## 8. Revision history

## Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
CGD944C_1	20070606	Product data sheet	-	-

#### 870 MHz, 25 dB gain power doubler amplifier

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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